



FQPF9N25CYDTU Information



For Reference Only

Part Number FQPF9N25CYDTU

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - SingleDescriptionMOSFET N-CH 250V 8.8A TO-220F

DescriptionMOSFET N-CH 250V 8.8A TO-220FPackageTO-220-3 Full Pack, Formed Leads

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQPF9N25CYDTU Specifications

Manufacturer Part Number Manufacturer Fairchild/ON Semiconductor Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Formed Leads Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Bask (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs January (Ciss) (Max) @ Vds Tiph Fe 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs January (Al) Alond (Al) Alond (Al) Bask (Tc) Alond (Al) To-220-3 Full Pack, Formed Leads Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Formed Leads Series QFET? FET Type N-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 710pF @ 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs A38W (Tc) Rds On (Max) @ Id, Vgs A39W mohm @ 4.4A, 10V Operating Temperature Jerus A38W (Tc) Mounting Type Through Hole Supplier Device Package TO-220-3 Full Pack, Formed Leads	Manufacturer Part Number	FQPF9N25CYDTU
Package TO-220-3 Full Pack, Formed Leads Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 8.8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 710pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 38W (Tc) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Full Pack, Formed Leads	Manufacturer	Fairchild/ON Semiconductor
PackageTO-220-3 Full Pack, Formed LeadsSeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C8.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds710pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs430 mOhm @ 4.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	Category	Discrete Semiconductor Products
Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 8.8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 710pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 38W (Tc) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C8.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds710pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs430 mOhm @ 4.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	Package	TO-220-3 Full Pack, Formed Leads
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C8.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds710pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs430 mOhm @ 4.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	Series	QFET?
Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C8.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds710pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs430 mOhm @ 4.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 710pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds710pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs430 mOhm @ 4.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 710pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Current - Continuous Drain (Id) @ 25°C	8.8A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 710pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 710pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 38W (Tc) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Gate Charge (Qg) (Max) @ Vgs	35nC @ 10V
FET Feature - Power Dissipation (Max) 38W (Tc) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Input Capacitance (Ciss) (Max) @ Vds	710pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 430 mOhm @ 4.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs430 mOhm @ 4.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Power Dissipation (Max)	38W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Rds On (Max) @ Id, Vgs	430 mOhm @ 4.4A, 10V
Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Formed Leads	Mounting Type	Through Hole
	Supplier Device Package	TO-220F-3 (Y-Forming)
Report errors?	Package / Case	TO-220-3 Full Pack, Formed Leads
1		Report errors?

FQPF9N25CYDTU Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQPF9N25CYDTU Payment Methods





















FQPF9N25CYDTU Shipping Methods













If you have any question about FQPF9N25CYDTU, please do not hesitate to contact us!

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